





is Surface micromachining technique in fabrication of MEMI.	Carrier,
First, polyimide is relectively deposited on the silicon substrate.	
Slicer water	
Silicon water water > Polymote deposited at sacrificial layer	septim residenting
02	parte a construir di suite
Then aluminium (film'is deposited via physical vapor deposition (PVD) on the scarficia	al
layer. Alyminium doponited sharing tool and all as Ild	
The edict problem to large un presentation en de dhat is used to everte any last	and the second second
The polyimide is then removed in a process called release	
> sacrificial layer removed of realising camplever	and the same of th
Most which protects use at the first to the protect of the pieceles	Telsivice of the A
injuted coming it to the arge space of the received with frame	
20) List of least 4: materials employed in fabrication of MEMS of miles	water to be a
Single-crystal cube silvebra carbides to la la lavorne sit of a dist	
Germanium - based material for example polycrystalline germanium and	COLUMN TO SERVICE SERV
poly ayutalline alicon qermanium.	and distribution
Metals and metal nanocomposites (gold, aluminum, mekel-iron, titanium-nicke	(1)
Ceramics Caluminium nitride, gallium nitred nitrade)	4
Rezoelectric moterialis applicable remains to 1944 with an and	e may resolve and
A began I lumidt bea gette da sitelier gegendete at the med the grandets with boy	
b) Explain MUMPs processing sequence and danger rules.	participant of the second
Design rules are supposed to ensure the greatest possibility of successful	na vesti dependi
fabrication They define the minimum feature sizes and spaces for all lovels	- considerate
and minimum overlap and maring between relevant levels.	termination of the state of
Hole layers (HOLEO, HOLE, HOLE 2 and HOLEN) APT POLYO, POLY: POLYE and METAL.	kin ilministra on structure
respectively are shown as separate levels in order to make layout of Politic	ls
POLY, POLY 2 and METAL, easier. These holes (excepts (Hole o) provide shorter	
POLY 1, POL 12 and MEINE, butter, miss factives and a way to extract	
release etch paths under large polysilion features, and a way to 'extract'	
holes from a light field level.	

Mnemonic level	CIF level	GDs Level	Nominal Line Space	Minimum feature	Minimum
* POLTO	EPZ	13	3.0	2.0	2.0
* ANCHOR!	COF	43	3.0	3.0	20
* DIMPLE	cos	50	3.0	2.0	3.0
* P0171	CPS	45	3.0	2.0	2.0
POLY 1 - POLY 2- VIA	COT	47	3.0	2.0	2.0
*ANCHOR 2	COL	52	3.0	3.0	2.0
*POLY 2	CPT	49	3.0	2.0	2.0
* METAL	GCM)	51	3.0	3.0	3.0
* HOLE O	CHZ	41	3.0	2.0	2.0
* HOLE !	Сно	0	4.0	3.0	3.0
* HOLE 2	СНТ	- 1	4.0	3.0	3.0
* HOLEM	CHM	48	5.0	4.0	4.0